NSN 5962-01-023-3275

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View Online at https://aerobasegroup.com/nsn/5962-01-023-3275

Body	Land	ıth.
DOUV	Leng	atm:

Between 0.350 inches and 0.400 inches

Body Width:

Between 0.200 inches and 0.300 inches

Body Height:

Between 0.008 inches and 0.100 inches

Maximum Power Dissipation Rating:

650.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Converter model 6514a

Features Provided:

Hermetically sealed and monolithic and positive outputs and w/enable and programmable and programmed and w/buffered output and w/decoded output

Inclosure Material:

Ceramic and glass

Inclosure Configuration:

Flat pack

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

6 input

Case Outline Source And Designator:

-0-004-ag joint electron device engineering council

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

50.00 nanoseconds propagation delay time, low to high level output and 50.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Memory Capacity:

Unknown

Test Data Document:

35351-151471 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

8 printed circuit

Shelf Life:

NI/o

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Demilitarization:

Yes - demil/mli

Fiig:

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